

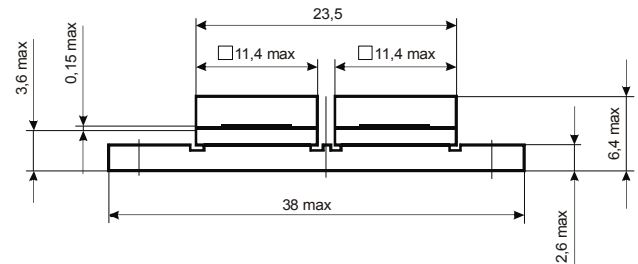
SynteZ Microelectronics

KT9151A

NPN SILICON RF POWER TRANSISTOR

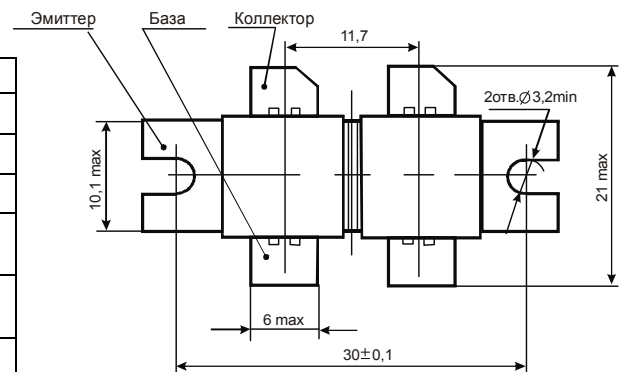
Designed for operation in linear
Class AB push-pull power amplifiers
of TV and aircraft radio transmitters

- Output power = 200 W , f = 225 MHz, $V_{CC} = 28$ V
- Power gain = 7 dB (min)



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	55	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	33	A
Operating Junction Temperature	T_j	+200	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	0.5	°C/W
Total Power Dissipation, $T_C = 25$ °C	P_D	350	W



Case KT-82

FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain ($V_{CC} = 28$ V, $P_{out} = 200$ W @ 1 dB Comp., f = 225 MHz)	G_P	7			dB
Collector Efficiency ($V_{CC} = 28$ V, $P_{out} = 200$ W, f = 225 MHz)	η_c	55			%

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Specification is subject to change without notice